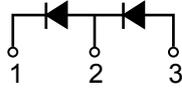
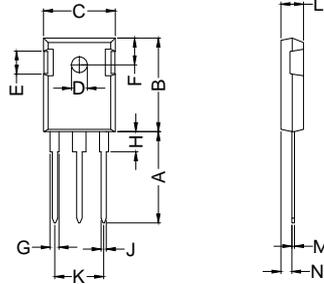


# SDD45N12

## Discrete Diodes



Dimensions TO-247AD



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.620	0.640
ØD	3.15	3.65	0.124	0.144
E	4.32	5.49	0.170	0.216
F	5.40	6.30	0.213	0.248
G	1.65	2.18	0.065	0.086
H	3.80	4.50	0.150	0.177
J	1.00	1.40	0.039	0.055
K	10.80	11.10	0.425	0.437
L	4.70	5.30	0.185	0.209
M	0.40	0.80	0.016	0.031
N	1.50	2.49	0.059	0.098

	V <sub>RSM</sub> V	V <sub>RRM</sub> V
<b>SDD45N02</b>	300	200
<b>SDD45N04</b>	500	400
<b>SDD45N08</b>	900	800
<b>SDD45N10</b>	1100	1000
<b>SDD45N12</b>	1300	1200
<b>SDD45N16</b>	1700	1600
<b>SDD45N18</b>	1900	1800
<b>SDD45N20</b>	2100	2000

Symbol	Test Conditions	Maximum Ratings	Unit
I <sub>F(AV)M</sub>	T <sub>C</sub> =130°C; 180°sine, per chip	45	A
I <sub>FSM</sub>	T <sub>VJ</sub> =45°C; V <sub>R</sub> =0V; t=10ms (50Hz), sine t=8.3ms (60Hz), sine	485 520	A
	T <sub>VJ</sub> =150°C; V <sub>R</sub> =0V; t=10ms(50Hz), sine t=8.3ms(60Hz), sine	415 445	
I <sup>2</sup> t	T <sub>VJ</sub> =45°C; V <sub>R</sub> =0V; t=10ms (50Hz), sine t=8.3ms (60Hz), sine	1160 1130	A <sup>2</sup> s
	T <sub>VJ</sub> =150°C; V <sub>R</sub> =0V; t=10ms(50Hz), sine t=8.3ms(60Hz), sine	850 810	
T <sub>VJ</sub> T <sub>VJM</sub> T <sub>stg</sub>		-40...+175 175 -55...+150	°C
M <sub>d</sub>	Mounting torque	0.8...1.2	Nm
Weight	Typical	6	g

Symbol	Test Conditions	Characteristic Values	Unit
I <sub>R</sub>	T <sub>VJ</sub> =T <sub>VJM</sub> ; V <sub>R</sub> =V <sub>RRM</sub>	< 1.00	mA
V <sub>F</sub>	I <sub>F</sub> =45A; T <sub>VJ</sub> =25°C	< 1.25	V
V <sub>FO</sub>	For power-loss calculations only	0.80	V
r <sub>F</sub>	T <sub>VJ</sub> =T <sub>VJM</sub>	9.0	mΩ
R <sub>thJC</sub> R <sub>thCH</sub>	DC current typical	0.55 0.20	K/W

- International Standard Package TO-247AD
- RoHS compliant
- Non-Isolated package
- Epoxy meets UL 94V-0

**Sirectifier®**

# SDD45N12

## Discrete Diodes

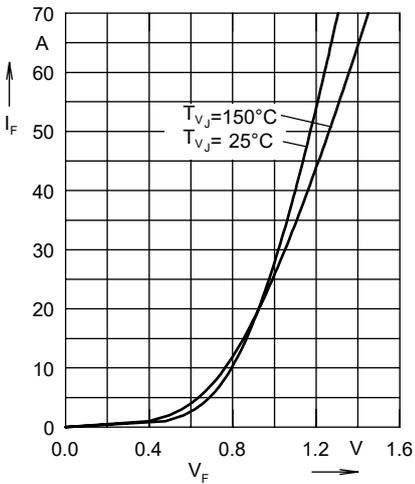


Fig. 1 Forward current versus voltage drop per diode

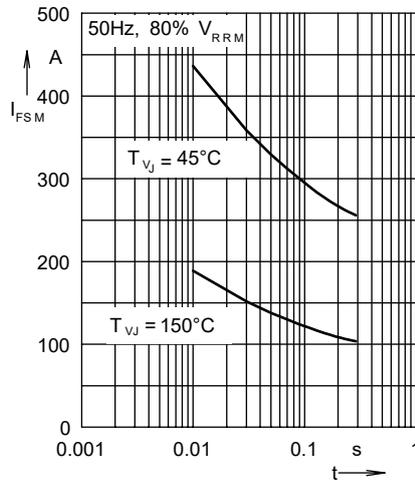


Fig. 2 Surge overload current

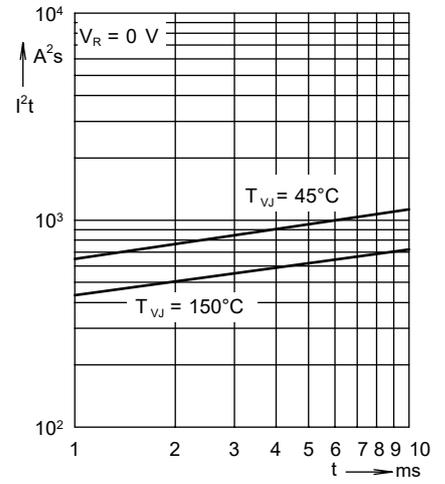


Fig. 3  $I^2t$  versus time per diode

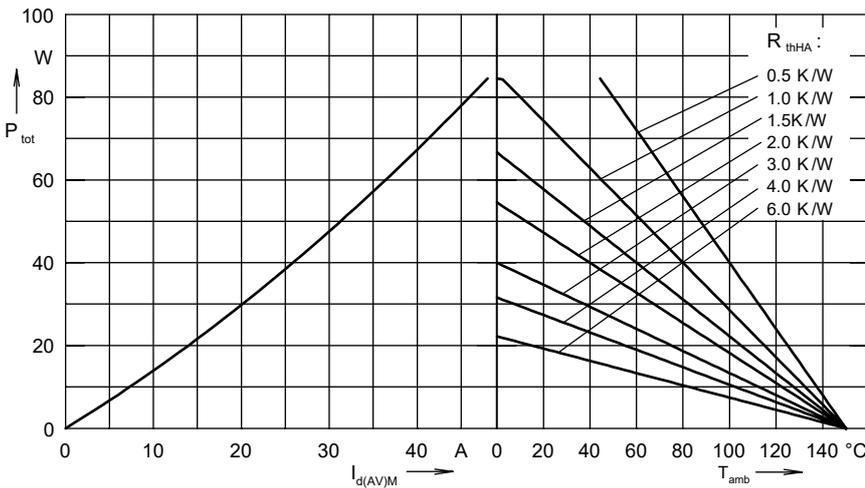


Fig. 4 Power dissipation versus direct output current and ambient temperature, sine 180°

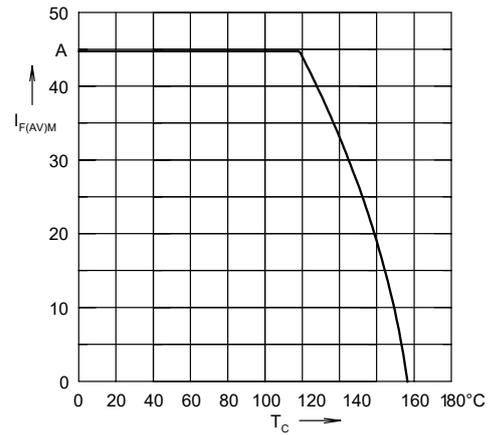


Fig. 5 Max. forward current versus case temperature

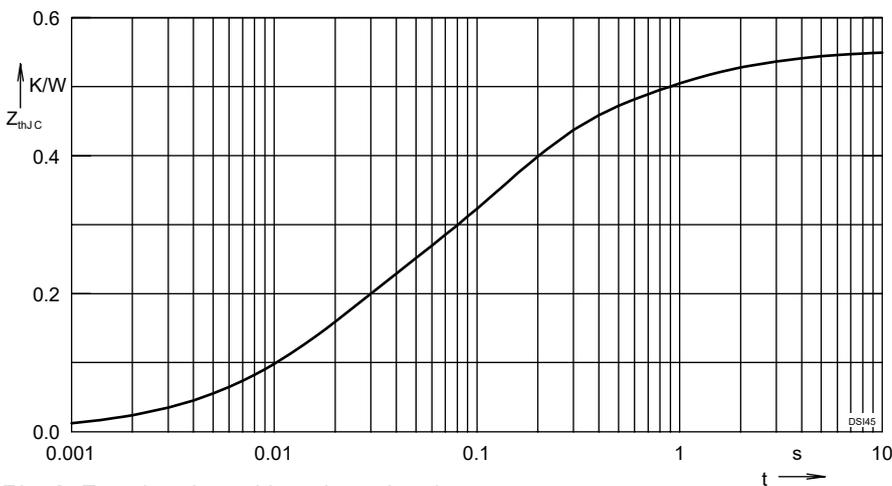


Fig. 6 Transient thermal impedance junction to case



Constants for  $Z_{thJC}$  calculation:

i	( $R_{thi}$ K/W)	$t_i$ (s)
1	0.033	0.0006
2	0.095	0.0039
3	0.164	0.0330
4	0.258	0.272